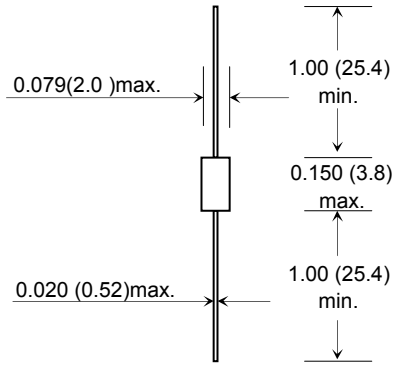
DB3, DB4

SILICON BI-DIRECTIONAL DIACS

V_{BR} : 32 - 40 Volts

DO - 35 Glass
(DO-204AH)



Dimensions in inches and (millimeters)

FEATURES :

* V_{BR} : 32 V and 40 V
* Low breakover current
* Pb / RoHS Free

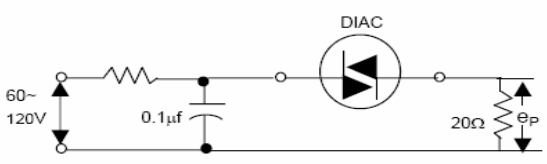
MECHANICAL DATA :

*** Case:** DO-35 Glass Case
*** Weight:** approx. 0.11g

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

RATING	SYMBOL	DB3	DB4	UNIT
Minimum Breakover Voltage	V_{BR1} and $V_{BR2\ (Min.)}$	28	35	V
Typical Breakover Voltage	V_{BR1} and $V_{BR2\ (Typ.)}$	32	40	V
Maximum Breakover Voltage	V_{BR1} and $V_{BR2\ (Max.)}$	36	45	V
Maximum Breakover Current	$I_{(BR)1}$ and $I_{(BR)2}$	200		μA
Maximum Breakover Voltage Symmetry	$[V_{(BR)1}] - [V_{(BR)2}]$	3.8		V
Minimum Dynamic Breakback Voltage $\Delta I = [I_{BR}$ to $I_F = 10$ mA]	$\lvert \Delta V \pm \rvert$	5.0		V
Maximum Peak Current at Ta = 50 °C (10 μs duration, 120 cycle repetition rate)	I_P	±2		A
Maximum Peak output Voltage at Ta = 50 °C **	e_P	±3		V
Thermal Impedance Junction to Ambient	RΘJA	60		°C/W
Operating Junction Temperature Range	TJ	- 40 to + 100		°C
Storage Temperature Range	TSTG	- 40 to + 150		°C

**CIRCUIT FOR PEAK OUTPUT VOLTAGE TEST



Characteristics at T_{amb} = 25°C

TYPICAL DIAC-TRIAC
FULL-WAVE PHASE CONTROL CIRCUIT

